BLV30

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV30** is Designed for Television Band IV & V Applications up to 860 MHz.

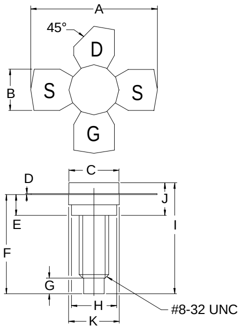
FEATURES:

- Common Emitter
- **P_G** = 10 dB at 2.0 W/860 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	1.5 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	15.9 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	10 ^{O}C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 10 mA	60			**V**
BV_{CEO}	I_C = 50 mA	30			**V**
BV_{EBO}	I_E = 4.0 mA	4.0			**V**
I_{CBO}	V_{CB} = 30 V			4.0	**mA**
h_{FE}	V_{CE} = 25 V I_C = 500 mA	15		120	**---**
C_{OB}	V_{CB} = 28 V f = 1.0 MHz			10	**pF**
P_G **IMD_1**	V_{CE} = 25 V I_C = 410 mA f = 860 MHz P_{OUT} = 2.0 W	10 -60			**dB** **dBc**